

## 8 Octands photodiode without hole

### Specifications

Detection material:	n/P, 10 ... 20 Ohmcm, 525 $\mu\text{m}$
Active area:	5.97 mm <sup>2</sup> per quadrant
Spectral range:	200 nm ... 1150 nm
Wavelength of peak response:	800 nm
Storage temperature:	-40 °C ... 150 °C
Dark current $I_{\text{R}}$ : (max at -5 V)	2 nA/mm <sup>2</sup>
Junction capacitance $C_{\text{j}}$ : (max at -5 V)	30 pF/mm <sup>2</sup>
Top bondpad material:	AlSi
Top bondpad size:	300 $\mu\text{m}$ $\times$ 300 $\mu\text{m}$
Bottom material:	AlSi